



## PNP SWITCHING SILICON TRANSISTOR

Qualified per MIL-PRF-19500/290

*Qualified Levels:*  
JAN, JANTX, JANTXV  
and JANS

### DESCRIPTION

This family of 2N2904AL and 2N2905AL switching transistors are military qualified up to the JANS level for high-reliability applications. These devices are also available in a TO-39 package. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

**Important:** For the latest information, visit our website <http://www.microsemi.com>.

### FEATURES

- JEDEC registered 2N2904 through 2N2905 series.
- JAN, JANTX, JANTXV, and JANS qualifications are available per MIL-PRF-19500/290. (See [part nomenclature](#) for all available options.)
- RoHS compliant versions available (commercial grade only).

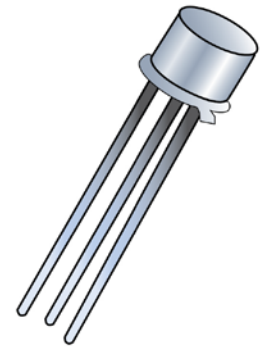
### APPLICATIONS / BENEFITS

- General purpose transistors for high speed switching applications.
- Military and other high-reliability applications.


### MAXIMUM RATINGS

Parameters / Test Conditions	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	V
Collector-Base Voltage	$V_{CBO}$	60	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	195	$^{\circ}\text{C}/\text{W}$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	50	$^{\circ}\text{C}/\text{W}$
Collector Current	$I_C$	600	mA
Total Power Dissipation	$P_T$	0.8 3.0	W
		@ $T_A = +25^{\circ}\text{C}$ <sup>(1)</sup> @ $T_C = +25^{\circ}\text{C}$ <sup>(2)</sup>	
Operating & Storage Junction Temperature Range	$T_J$ and $T_{stg}$	-65 to +200	$^{\circ}\text{C}$

- Notes:**
1. For derating, see [figures 1 and 2](#).
  2. For thermal impedance, see [figures 3 and 4](#).



**TO-5 Package**

Also available in:  
**TO-39 (TO-205AD) package**  
(long-leaded)  
 [2N2904 & 2N2905A](#)

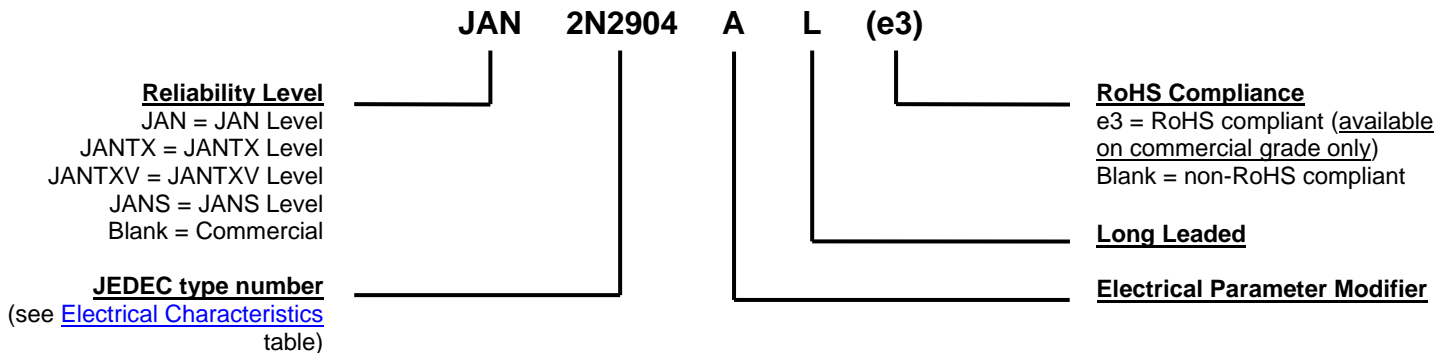
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**MECHANICAL and PACKAGING**

- CASE: Hermetically sealed, kovar base, nickel cap.
- TERMINALS: Tin/lead plate or RoHS compliant matte/tin (commercial grade only) over nickel.
- MARKING: Part number, date code, manufacturer's ID.
- POLARITY: PNP (see package outline).
- WEIGHT: Approximately 1.14 grams.
- See [Package Dimensions](#) on last page.

**PART NOMENCLATURE**

**SYMBOLS & DEFINITIONS**

Symbol	Definition
$C_{obo}$	Common-base open-circuit output capacitance.
$I_{CEO}$	Collector cutoff current, base open.
$I_{CEX}$	Collector cutoff current, circuit between base and emitter.
$I_{EBO}$	Emitter cutoff current, collector open.
$h_{FE}$	Common-emitter static forward current transfer ratio.
$V_{CEO}$	Collector-emitter voltage, base open.
$V_{CBO}$	Collector-emitter voltage, emitter open.
$V_{EBO}$	Emitter-base voltage, collector open.

**ELECTRICAL CHARACTERISTICS @  $T_A = +25\text{ }^\circ\text{C}$ , unless otherwise noted**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Current $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	60		V
Collector-Emitter Cutoff Voltage $V_{CE} = 60\text{ V}$	$I_{CES}$		1.0	$\mu\text{A}$
Collector-Base Cutoff Current $V_{CB} = 60\text{ V}$ All Types	$I_{CBO1}$		10	$\mu\text{A}$
$V_{CB} = 50\text{ V}$ 2N2904AL, 2N2905AL	$I_{CBO2}$		10	nA
$V_{CB} = 50\text{ V @ } T_A = +150\text{ }^\circ\text{C}$ 2N2904AL, 2N2905AL	$I_{CBO3}$		10	$\mu\text{A}$
Collector-Base Cutoff Current $V_{CB} = 50\text{ V}$	$I_{CBO}$		10	nA
$V_{CB} = 60\text{ V}$			10	$\mu\text{A}$
Emitter-Base Cutoff Current $V_{EB} = 3.5\text{ V}$	$I_{EBO}$		50	nA
$V_{EB} = 5.0\text{ V}$			10	$\mu\text{A}$
<b>ON CHARACTERISTICS <sup>(1)</sup></b>				
Forward-Current Transfer Ratio $I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$		2N2904AL	40	
		2N2905AL	75	
$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$	$h_{FE}$	2N2904AL	40	175
		2N2905AL	100	450
$I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$		2N2904AL	40	
		2N2905AL	100	
$I_C = 150\text{ mA}, V_{CE} = 10\text{ V}$		2N2904AL	40	120
		2N2905AL	100	300
$I_C = 500\text{ mA}, V_{CE} = 10\text{ V}$		2N2904AL	40	
		2N2905AL	50	
Collector-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$	$V_{CE(sat)}$		0.4	V
$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			1.6	
Base-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$	$V_{BE(sat)}$		1.3	V
$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			2.6	

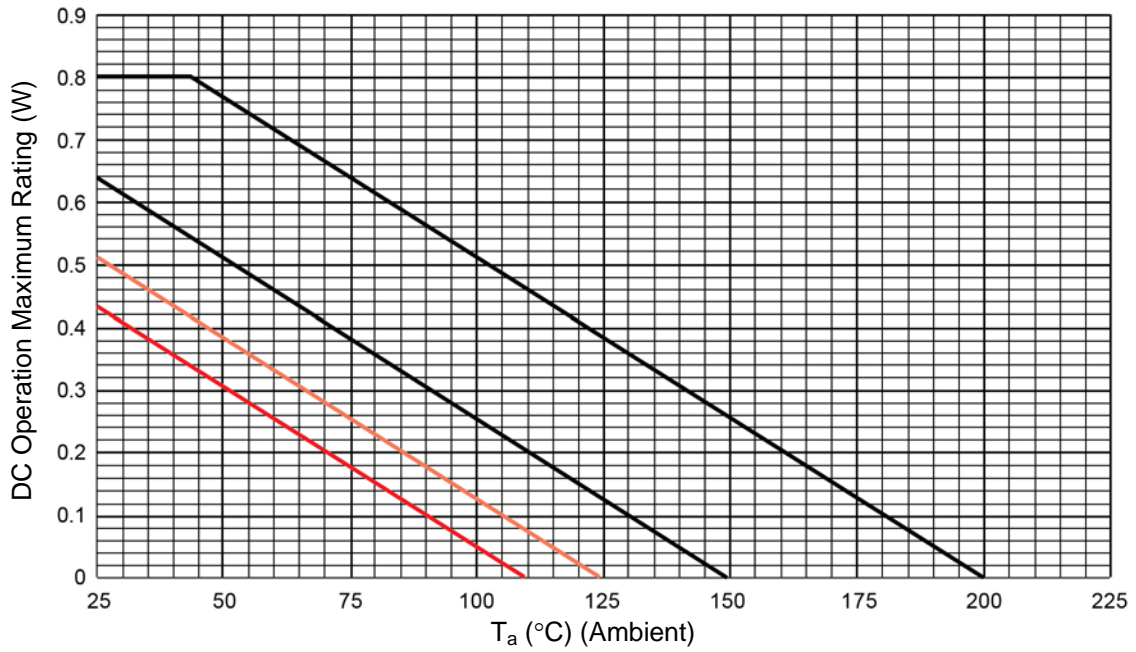
(1) Pulse Test: Pulse Width = 300  $\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .

**ELECTRICAL CHARACTERISTICS @  $T_A = +25\text{ }^\circ\text{C}$ , unless otherwise noted (continued)**
**DYNAMIC CHARACTERISTICS**

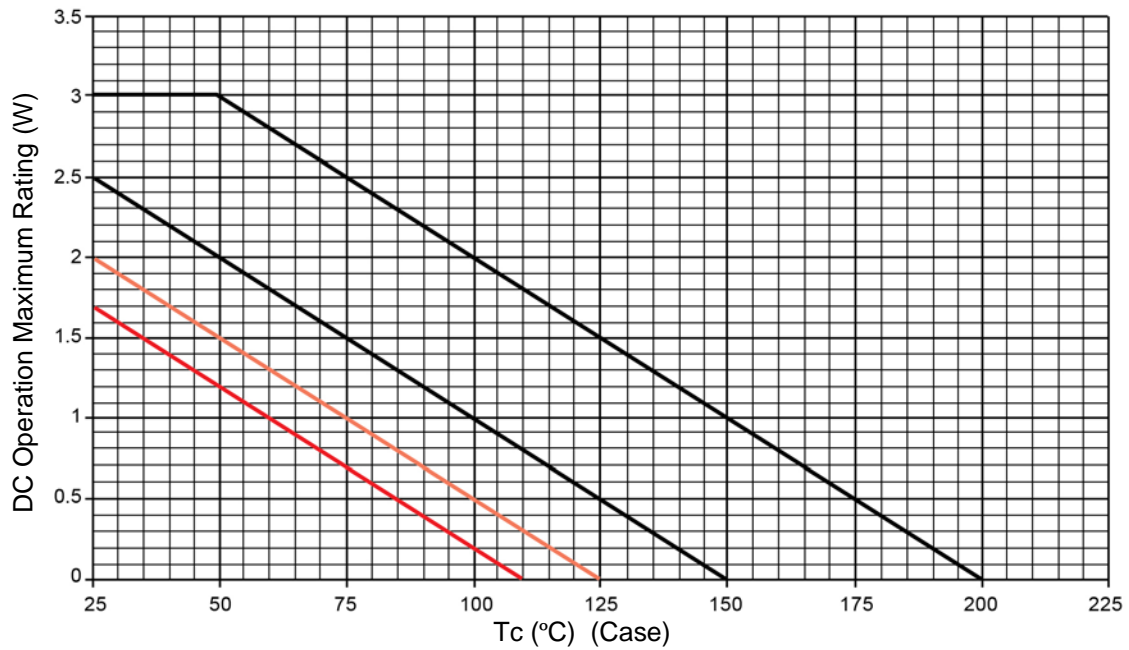
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward-Current Transfer Ratio $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ V}$ , $f = 1.0\text{ kHz}$	$h_{fe}$		100	
Small-Signal Short-Circuit Forward-Current Transfer Ratio $I_C = 50\text{ mA}$ , $V_{CE} = 20\text{ V}$ , $f = 100\text{ MHz}$	$ h_{fe} $		2.0	
Output Capacitance $V_{CB} = 10\text{ V}$ , $I_E = 0$ , $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	$C_{obo}$		8.0	pF
Input Capacitance $V_{EB} = 2.0\text{ V}$ , $I_C = 0$ , $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	$C_{ibo}$		30	pF

**SWITCHING CHARACTERISTICS**

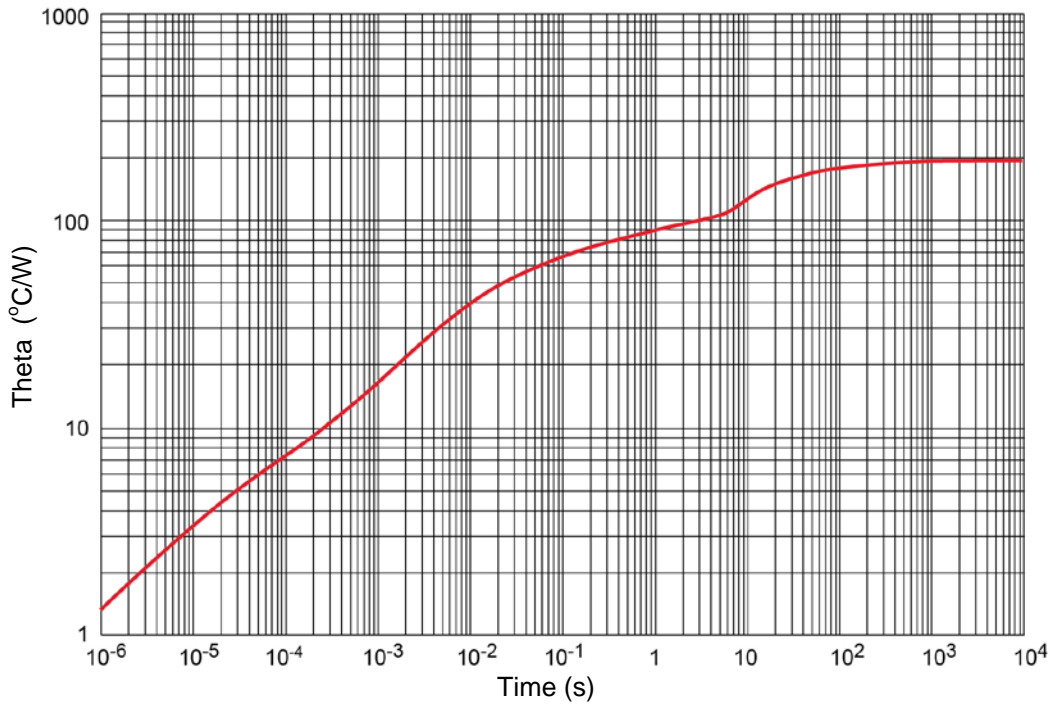
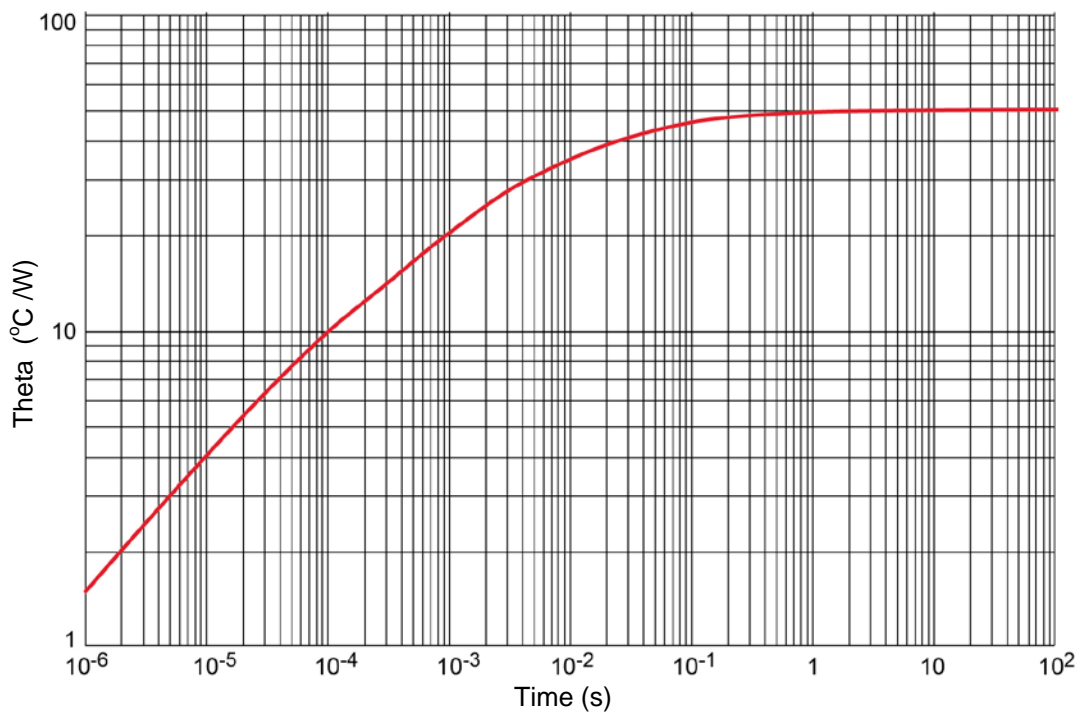
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time	$t_{on}$		45	ns
Turn-Off Time	$t_{off}$		300	ns

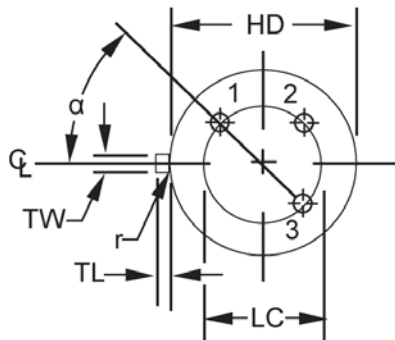
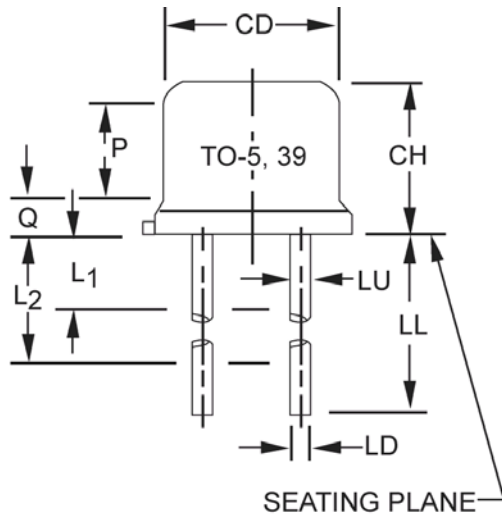
**GRAPHS**


**FIGURE 1**  
Derating (R<sub>θJA</sub>) PCB



**FIGURE 2**  
Derating (R<sub>θJA</sub>) PCB

**GRAPHS (continued)**

**FIGURE 3**
Thermal impedance graph ( $R_{\theta JA}$ )

**FIGURE 4**
Thermal impedance graph ( $R_{\theta JA}$ )

**PACKAGE DIMENSIONS**


Symbol	Dimensions				Note
	Inch		Millimeters		
	Min	Max	Min	Max	
<b>CD</b>	0.305	0.335	7.75	8.51	
<b>CH</b>	0.240	0.260	6.10	6.60	
<b>HD</b>	0.335	0.370	8.51	9.40	
<b>LC</b>	0.200 TP		5.08 TP		6
<b>LD</b>	0.016	0.021	0.41	0.53	7, 8
<b>LL</b>	0.500	0.750	12.70	19.05	7, 8, 12
<b>LU</b>	0.016	0.019	0.41	0.48	7, 8
<b>L1</b>		0.050		1.27	7, 8
<b>L2</b>	0.250		6.35		7, 8
<b>P</b>	0.100		2.54		
<b>Q</b>		0.050		1.27	5
<b>TL</b>	0.029	0.045	0.74	1.14	4
<b>TW</b>	0.028	0.034	0.71	0.86	3
<b>r</b>		0.010		0.25	10
<b>α</b>	45° TP		45° TP		6

**NOTES:**

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
7. Dimension LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi$ x symbology.
12. For "L" suffix devices, dimension LL is 1.50 (38.10 mm) minimum, 1.75 (44.45 mm) maximum.
13. Lead 1 = emitter, lead 2 = base, lead 3 = collector.